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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電 気 的 特 性 (T _b =25°C)										外形	備考	
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μS)	f _{αb} f _r * (Mc)			C _{ob} (pF)
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
- 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外形	備考								
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値		直流又はパルス hFE		バイアス		h _{je}	h _{ie} h _{ib} * (Ω)	h _{re} h _{rs} * (×10 ⁻⁴)	h _{oe} h _{os} * (μT)	f _{ωB} f _T * (Mc)			C _{ob} (pF)	F _{βB} h _{ie} (real)* (Ω)						
									(μA)	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _E (mA)										h _{fb} *					
2SA593																													
" 594	東芝日電	RF.SW	Si.E	-60	-5	-200	750	175	-0.1	-45	40~240	-1	-10	-10	10									200*	3.5	<120*	84B	2SC594 とコンプリ	
" 595																													
" 596																													
" 597	東芝	RF.PA	Si.EP	-50	-4	-1A	6 W (T _c =25°C)	175	-1	-30	50	-3	-150	-10	100									400*	10	10*	84B		
" 598																													
" 599																													
" 600																													
" 601																													
" 602																													
" 603	日電	RF.SW	Si.E	-60	-8	-200	300	150	-0.5	-40	140	-1	-10	-10	10									250*	7.5	70	49C	2SC943 とコンプリ	
★ " 604	"	"	"	-120	-5	-30	300	150	-0.5	-100	80	-3	-1	-10	10									170*	3	20	49C		
★ " 605	"	RF.SW	"	-180	-5	-50	300	150	-1	-100	100	-6	-15	-10	10									100*	4	40	49C		
★ " 606	"	PA	"	-100	-5	-700	700	150	-3	-80	100	-5	-200	-10	100									>50*	<50	45*	84B	2SC959 とコンプリ	
★ " 607	"	"	"	-100	-5	-700	1 W	150	-3	-80	80	-5	-200	-10	100									>50*	<50	45*	97B	2SC960 とコンプリ	
★ " 608	三洋	RF.AF.SW	Si.EP	-40	-5	-100	100	125	-1	-25	150	-6	-1	-6	10									180*	7	C _c F _{ωB} 100pS	138		
★ " 609	"	RF.AF	"	-30	-5	-100	100	125	-1	-25	85	-6	-1	-6	1									80*	7	C _c F _{ωB} 100pS	27		
" 610	新日無	"	"	-30	-5	-100	150	125	-1	-20	100	-6	-1	-6		5000	1.5	20						170*	3.3	C _c F _{ωB} 50pS	27		
" 611	"	"	"	-60	-5	-100	150	125	-1	-20	100	-6	-1	-6	1	5000	1.5	20						170*	3.3	C _c F _{ωB} 50pS	27		
" 612	"	RF.SW	"	-90	-5	-50	200	175	-1	-70	100	-6	-1	-10	2									150*	4	C _c F _{ωB} 50pS	243		
★ " 613	日電	PA	Si.E	-60	-7	-1A	15W (T _c =25°C)	150	-1mA	-40	80	-5	-500	-10	200										30*	60	140*	134	2SD150 とコンプリ
★ " 614	"	"	"	-80	-7	-1A	15W (T _c =25°C)	150	-1mA	-60	80	-5	-500	-10	200										30*	60	140*	134	
" 615																													
★ " 616	日電	PA	Si.EMe	-80	-5	-3A	25W (T _c =25°C)	150	-1mA	-60	70	-5	-1A	-10	200										15*	100	60*	134	2SD155 とコンプリ
" 617	日立	RF	Si.T	-150	-5	-50	200	175	-1	-100	80	-3	-15	-10	10										60*	3.5	C _c F _{ωB} 40pS	244	
" 618	"	"	"	-180	-5	-50	200	175	-1	-150	80	-3	-15	-10	10										60*	3.5	C _c F _{ωB} 40pS	244	
" 619																													
" 620	新日無	RF.AF.LN	Si.EP	-30	-5	-50	200	175	-50nA	-20	250	-6	-1	-6	0.3	190	21k	3.4	6.2						120*	3	C _c F _{ωB} 55pS	243	
" 621	"	RF.AF	"	-60	-5	-200	400	175	-0.5	-20	80	-1	-50	-10	5										200*	6	C _c F _{ωB} 50pS	84B	
" 622	"	SW	Si.EP ゲーラフロン	-30	-10	-300	150	125	-0.1	-20	40,000	-6	-100																

t_{on} < 600nS, t_{off} < 1.2μS
t_{rr} < 600nS